

**Amendment to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-45 (Canceled)

46. (New) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip:

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing the main surface of the semiconductor chip, a second surface opposite to the first surface and a through hole provided thereof;

a plurality of conductive patterns formed on the first surface of the base resin film, the conductive patterns extending near the through hole; and

an insulating film formed on the first surface of the base resin film and the conductive patterns, the insulating film having a plurality of electrode holes for exposing a part of the conductive patterns through the through holes.

47. (New) A semiconductor device according to claim 46, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

48. (New) A semiconductor device according to claim 46, further comprising a plurality of solder balls formed on the electrode holes.
49. (New) A semiconductor device according to claim 46, wherein the base resin film is formed on the main surface, back surface and side surface of the semiconductor chip.
50. (New) A semiconductor device according to claim 46, wherein the base resin film is covered by elastic resin.
51. (New) A semiconductor device according to claim 50, wherein the elastic resin is polyimide.
52. (New) A semiconductor device comprising:  
a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;  
a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface said semiconductor chip, a second surface opposite to the first surface and a through hole provided thereof;

a plurality of conductive patterns formed on the second surface opposite the first surface and a through hole provided thereof;

a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns extending near the through hole;

an insulating film formed on the second surface of the base resin film and conductive patterns, the insulating film having a plurality of electrodes holes for exposing a part of the conductive patterns; and

a plurality inner leads connecting the electrodes with the conductive patterns through the through holes.

53. (New) A semiconductor device according to claim 52, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

54. (New) A semiconductor device according to claim 52. further comprising a plurality of solder balls formed on the electrodes holes.

55. (New) A semiconductor device according to claim 52, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

56. (New) A semiconductor device according to claim 52, wherein the base resin film is covered by elastic resin.

57. (New) A semiconductor device according to claim 56, wherein the elastic resin is polyimide.

58. (New) A semiconductor device comprising:  
a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;  
a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip, the base resin film having a first surface facing said semiconductor chip and a second surface opposite the first surface;  
a plurality of electrode patterns formed on the first surface of the base resin film;  
a first insulating film formed on the first surface of the base resin film, the first insulating film having a plurality of first electrode holes for exposing the electrode patterns;  
a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns electrically connected to the electrode patterns; and

a second insulating film formed on the second surface of the base resin film and the conductive patterns, the insulating film having a plurality of second electrode holes for exposing a part of the conductive patterns.

59. (New) A semiconductor device according to claim 58, wherein the main surface and the side surface of the semiconductor chip are covered by molding resin.

60. (New) A semiconductor device according to claim 58, further comprising a plurality of solder balls formed on the second electrodes holes.

61. (New) A semiconductor device according to claim 58, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

62. (New) A semiconductor device according to claim 61, wherein the base resin film is substantially surrounding the semiconductor chip.

63. (New) A semiconductor device according to claim 58, wherein the base resin is covered by elastic resin.

64. (New) A semiconductor device according to claim 63, wherein the elastic resin is polyimide.